

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 7 (Canceled).

Claim 8 (Currently Amended): An optical semiconductor device comprising
an optical multilayer film that is located on ~~a light incident plane or~~ a light emitting plane of
an optical semiconductor chip,

the optical multilayer film having a laminated structure that at least includes a first layer, a
second layer containing titanium oxynitride as a main component, and a third layer containing
magnesium fluoride as a main component, the first layer having a different refractive index from that
of the second layer or the third layer, the third layer being most removed from ~~the light incident plane~~
~~or the light emitting plane~~,

the laminated structure having a plurality reflection planes,

the thickness of the third layer being less than 1/4 of the wavelength of ~~light incident to the~~
~~light incident plane or~~ of light emitting from the light emitting plane converted into an optical
distance, and

tensile stresses and compressive stresses of the first, second, and third layers substantially

canceling each other.

Claim 9 (Original): The optical semiconductor device as claimed in claim 8, wherein the first layer and the second layer are in contact with each other.

Claim 10 (Original): The optical semiconductor device as claimed in claim 8, wherein another layer is interposed between the first layer and the second layer.

Claim 11 (Original): The optical semiconductor device as claimed in claim 8, wherein: the first layer contains magnesium fluoride; and
the second layer is sandwiched by the first layer and the third layer.

Claim 12 (Original): The optical semiconductor device as claimed in claim 8, wherein the first layer contains silicon oxide as a main component.

Claim 13 (Original): The optical semiconductor device as claimed in claim 8, wherein the optical multilayer film is a reflection preventing film or a highly reflective film.

Claim 14 (Original): The optical semiconductor device as claimed in claim 8, wherein the second layer is a layer formed by ion-assisted deposition.

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Claim 15 (Currently Amended): The optical semiconductor device as claimed in claim 8, wherein at least ~~the light incident plane or~~ the light emitting plane is sealed with resin.

Claim 16 - 19 (Canceled)

Claim 20 (Original): The optical semiconductor device as claimed in claim 8, further comprising a fourth layer having a refractive index higher than that of the first layer.